# National Accreditation Board for Testing and Calibration Laboratories

## SCOPE OF ACCREDITATION

**Laboratory Name :** HIREL LABORATORY, CONTINENTAL DEVICE INDIA PRIVATE LIMITED, C-120, NARAINA INDUSTRIAL AREA, NEW DELHI, DELHI, INDIA

**Accreditation Standard** ISO/IEC 17025:2017

**Certificate Number** TC-6266 **Page No** 1 of 10

**Validity** 16/11/2022 to 15/11/2024 **Last Amended on** -

| S.No | Discipline / Group | Materials or Products tested | Component, parameter or characteristic tested / Specific Test Performed / Tests or type of tests performed | Test Method Specification against which tests are performed and / or the techniques / equipment used |
|---|---|---|---|---|
| Permanent Facility | | | | |
| 1 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Autoclave or Pressure Cooker Test-Breakdown Voltage (VZ) | JESD-22 A102E |
| 2 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Autoclave or Pressure Cooker Test-Forward Voltage, (VF) | JESD-22 A102E |
| 3 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Autoclave or Pressure Cooker Test-Leakage Current, (IR) | JESD-22 A102E |
| 4 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Autoclave or Pressure Cooker Test-Zener Impedance, RD | JESD-22 A102E |
| 5 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | High Temp. Storage Forward-Breakdown Voltage (VZ) | MIL-STD 750F, 1031.5 |
| 6 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | High Temp. Storage Forward-Forward Voltage, (VF) | MIL-STD 750F, 1031.5 |
| 7 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | High Temp. Storage Forward-Leakage Current ,(IR) | MIL-STD 750F, 1031.5 |
| 8 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | High Temp. Storage Forward-Zener Impedance, RD | MIL-STD 750F, 1031.5 |

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| 9 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | HTRB (High Temp. Reverse Bias)-Breakdown Voltage (VZ) | MIL-STD 750F-1038.5 |
| 10 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | HTRB (High Temp. Reverse Bias)-Forward Voltage, (VF) | MIL-STD 750F-1038.5 |
| 11 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | HTRB (High Temp. Reverse Bias)-Leakage Current ,(IR) | MIL-STD 750F-1038.5 |
| 12 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | HTRB (High Temp. Reverse Bias)-Zener Impedance,RD | MIL-STD 750F-1038.5 |
| 13 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | IOPL (Intermittent Operating Life Test)-Breakdown Voltage (VZ) | MIL- STD 750F-1036.3 |
| 14 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | IOPL (Intermittent Operating Life Test)-Forward Voltage, (VF) | MIL- STD 750F-1036.3 |
| 15 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | IOPL (Intermittent Operating Life Test)-Leakage Current, (IR) | MIL- STD 750F-1036.3 |
| 16 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | IOPL (Intermittent Operating Life Test)-Zener Impedance, RD | MIL- STD 750F-1036.3 |
| 17 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Operating Life Test-Breakdown Voltage (VZ) | MIL-STD 750F-1026.5 |

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| 18 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Operating Life Test-Forward Voltage, (VF) | MIL-STD 750F-1026.5 |
| 19 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Operating Life Test-Leakage Current, (IR) | MIL-STD 750F-1026.5 |
| 20 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Operating Life Test-Zener Impedance, RD | MIL-STD 750F-1026.5 |
| 21 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Resistance to soldering heat-Breakdown Voltage (VZ) | MIL-STD750F-2031 |
| 22 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Resistance to soldering heat-Forward Voltage, (VF) | MIL-STD750F-2031 |
| 23 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Resistance to soldering heat-Leakage Current, (IR) | MIL-STD750F-2031 |
| 24 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Resistance to soldering heat-Zener Impedance, RD | MIL-STD750F-2031 |
| 25 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Robustness of Terminations | MIL-STD 750F-2036.5 |
| 26 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Seal Test | MIL- STD 750F-1071.14 Gross Leak Method D Fine Leak H1 and H2 |

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| 27 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Solderability Test | MIL- STD 750F-2026.12 |
| 28 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Steady State Temperature Humidity Bias Life Test-Breakdown Voltage (VZ) | JESD- 22 A101D |
| 29 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Steady State Temperature Humidity Bias Life Test-Forward Voltage, (VF) | JESD-22 A101D |
| 30 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Steady State Temperature Humidity Bias Life Test-Leakage Current, (IR) | JESD-22 A101D |
| 31 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Steady State Temperature Humidity Bias Life Test-Zener Impedance, RD | JESD-22 A101D |
| 32 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Temperature Cycling-Breakdown Voltage (VZ) | MIL-STD 750F-1051.9 |
| 33 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Temperature Cycling-Forward Voltage, (VF) | MIL-STD 750F-1051.9 |
| 34 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Temperature Cycling-Leakage Current, (IR) | MIL-STD 750F-1051.9 |
| 35 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Temperature Cycling-Zener Impedance, RD | MIL-STD 750F-1051.9 |

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| 36 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Thermal Shock-Breakdown Voltage (VZ) | MIL-STD 750F-1056.8 |
| 37 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Thermal Shock-Forward Voltage, (VF) | MIL-STD 750F-1056.8 |
| 38 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Thermal Shock-Leakage Current, (IR) | MIL-STD 750F-1056.8 |
| 39 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Diode | Thermal Shock-Zener Impedance, RD | MIL-STD 750F-1056.8 |
| 40 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Autoclave or Pressure Cooker Test-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | JESD-22 A102E |
| 41 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Autoclave or Pressure Cooker Test-DC Gain (h FE) | JESD-22 A102E |
| 42 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Autoclave or Pressure Cooker Test-Forward Voltage, (VFBE/VFEC/VFBC) | JESD-22 A102E |
| 43 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Autoclave or Pressure Cooker Test-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | JESD-22 A102E |
| 44 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Autoclave or Pressure Cooker Test-Saturation Voltage VCE(SAT)/VBE(SAT) | JESD-22 A102E |

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| 45 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | High Temp. Storage-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD 750F-1031.5 |
| 46 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | High Temp. Storage-DC Gain (h FE) | MIL-STD 750F-1031.5 |
| 47 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | High Temp. Storage-Forward Voltage (VFBE/VFEC/VFBC) | MIL-STD 750F-1031.5 |
| 48 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | High Temp. Storage-Leakage Current,(ICEO/ICBO/IEBO/ICEX) | MIL-STD 750F-1031.5 |
| 49 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | High Temp. Storage-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD 750F-1031.5 |
| 50 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | HTRB (High Temp. Reverse Bias)-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD750F-1039.4 |
| 51 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | HTRB (High Temp. Reverse Bias)-DC Gain (h FE) | MIL-STD750F-1039.4 |
| 52 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | HTRB (High Temp. Reverse Bias)-Forward Voltage, (VFBE/VFEC/VFBC) | MIL-STD750F-1039.4 |
| 53 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | HTRB (High Temp. Reverse Bias)-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD750F-1039.4 |

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| 54 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | HTRB (High Temp. Reverse Bias)-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD750F-1039.4 |
| 55 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | IOPL (Intermittent Operating Life Test)-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD 750F-1036.3 |
| 56 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | IOPL (Intermittent Operating Life Test)-DC Gain (h FE) | MIL-STD 750F-1036.3 |
| 57 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | IOPL (Intermittent Operating Life Test)-Forward Voltage, (VFBE/VFEC/VFBC) | MIL-STD 750F-1036.3 |
| 58 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | IOPL (Intermittent Operating Life Test)-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD 750F-1036.3 |
| 59 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | IOPL (Intermittent Operating Life Test)-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD 750F-1036.3 |
| 60 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Operating Life Test-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD 750F-1026.5 |
| 61 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Operating Life Test-DC Gain (h FE) | MIL-STD 750F-1026.5 |
| 62 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Operating Life Test-Forward Voltage (VFBE/VFEC/VFBC) | MIL-STD 750F-1026.5 |

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| 63 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Operating Life Test-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD 750F-1026.5 |
| 64 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Operating Life Test-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD 750F-1026.5 |
| 65 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Resistance to soldering heat-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD750F-2031.5 |
| 66 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Resistance to soldering heat-DC Gain (h FE) | MIL-STD750F-2031.5 |
| 67 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Resistance to soldering heat-Forward Voltage, (VFBE/VFEC/VFBC) | MIL-STD750F-2031.5 |
| 68 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Resistance to soldering heat-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD750F-2031.5 |
| 69 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Resistance to soldering heat-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD750F-2031.5 |
| 70 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Robustness of Terminations | MIL-STD 750F-2036.5 |
| 71 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Seal Test | MIL-STD750F-1071.14 Gross Leak Method D Fine Leak H1 and H2 |

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| 72 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Solderability Test | MIL-STD 750F-2026 |
| 73 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Steady State Temperature Humidity Bias Life Test-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | JESD- 22 A101D |
| 74 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Steady State Temperature Humidity Bias Life Test-DC Gain (h FE) | JESD-22 A101D |
| 75 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Steady State Temperature Humidity Bias Life Test-Forward Voltage, (VFBE/VFEC/VFBC) | JESD-22 A101D |
| 76 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Steady State Temperature Humidity Bias Life Test-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | JESD-22 A101D |
| 77 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Steady State Temperature Humidity Bias Life Test-Saturation Voltage VCE(SAT)/VBE(SAT) | JESD-22 A101D |
| 78 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Temperature Cycling-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD750F-1051.9 |
| 79 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Temperature Cycling-DC Gain (h FE) | MIL-STD750F-1051.9 |
| 80 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Temperature Cycling-Forward Voltage, (VFBE/VFEC/VFBC) | MIL-STD750F-1051.9 |

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| 81 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Temperature Cycling-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD750F-1051.9 |
| 82 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Temperature Cycling-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD750F-1051.9 |
| 83 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Thermal Shock-Breakdown Voltage (VCEO/VCBO/VEBO/VCEX) | MIL-STD 750F-1056.8 |
| 84 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Thermal Shock-DC Gain (h FE) | MIL-STD 750F-1056.8 |
| 85 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Thermal Shock-Forward Voltage, (VFBE/VFEC/VFBC) | MIL-STD 750F-1056.8 |
| 86 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Thermal Shock-Leakage Current, (ICEO/ICBO/IEBO/ICEX) | MIL-STD 750F-1056.8 |
| 87 | ELECTRONICS-ELECTRONIC COMPONENTS & EQUIPMENT SUB ASSEMBLIES | Transistor | Thermal Shock-Saturation Voltage VCE(SAT)/VBE(SAT) | MIL-STD 750F-1056.8 |